

## 30V N-Ch Power MOSFET

### Feature

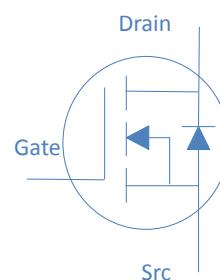
- ◇ High Speed Power Switching, Logic Level
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

$V_{DS}$		30	V
$R_{DS(on),typ}$	$V_{GS}=10V$	19	mΩ
$R_{DS(on),typ}$	$V_{GS}=4.5V$	30	mΩ
$I_D$ (Silicon Limited)		6	A

### Application

- ◇ Hard Switching and High Speed Circuit
- ◇ DC/DC in Telecoms and Industrial

SOT-23



Part Number	Package	Marking
HTJ270N03	SOT23	14

### Absolute Maximum Ratings at $T_J=25^{\circ}C$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_A=25^{\circ}C$	6	A
		$T_A=70^{\circ}C$	4	
Drain to Source Voltage	$V_{DS}$	-	30	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	24	A
Power Dissipation	$P_D$	$T_A=25^{\circ}C$	1.25	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 150	$^{\circ}C$

### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	100	$^{\circ}C/W$

**Electrical Characteristics at  $T_j=25^\circ\text{C}$  (unless otherwise specified)**
**Static Characteristics**

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.7	3.0	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=24V, T_j=25^\circ\text{C}$	-	-	1	$\mu A$
		$V_{GS}=0V, V_{DS}=20V, T_j=125^\circ\text{C}$	-	-	10	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6A$	-	19	27	$m\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	30	40	
Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=6A$	-	12	-	S

**Dynamic Characteristics**

Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=15V, f=1\text{MHz}$	-	522	-	pF
Output Capacitance	$C_{oss}$		-	105	-	
Reverse Transfer Capacitance	$C_{rss}$		-	82	-	
Total Gate Charge	$Q_g$	$V_{DD}=15V, I_D=6A, V_{GS}=10V$	-	10.9	-	nC
Gate to Source Charge	$Q_{gs}$		-	1.75	-	
Gate to Drain (Miller) Charge	$Q_{gd}$		-	3.4	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A, V_{GS}=10V, R_G=6\Omega,$	-	8	-	ns
Rise time	$t_r$		-	7	-	
Turn off Delay Time	$t_{d(off)}$		-	15	-	
Fall Time	$t_f$		-	10	-	

**Reverse Diode Characteristics**

Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_F=2A$	-		1.2	V
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Fig 1. Typical Output Characteristics

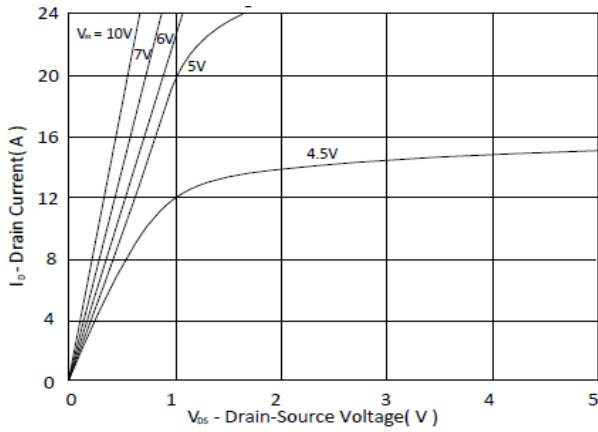


Figure 2. On-Resistance vs. Gate-Source Voltage

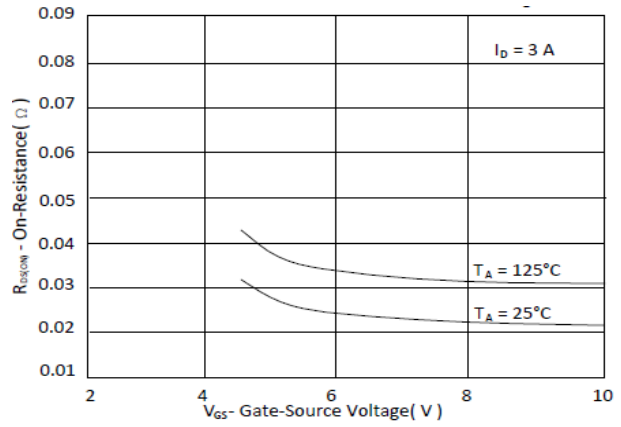


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

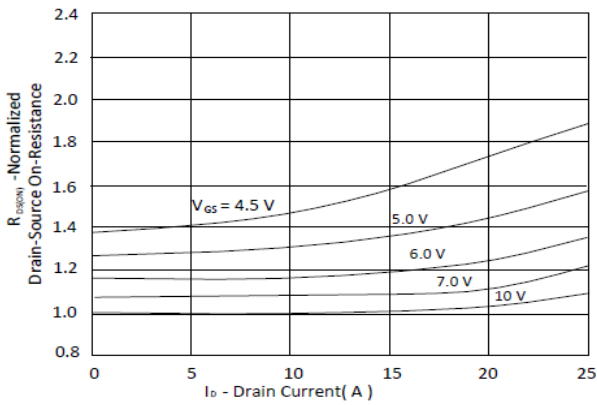


Figure 4. On-Resistance vs. Junction Temperature

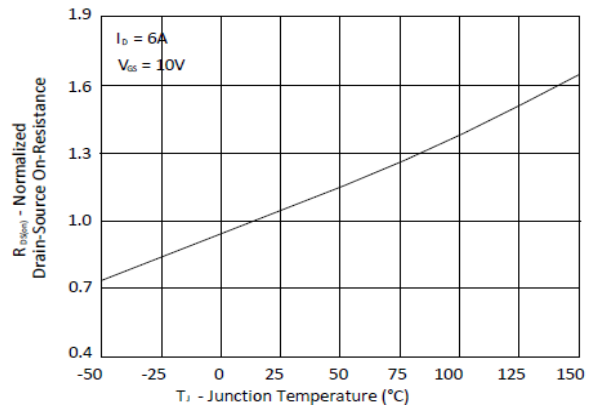


Figure 5. Typical Transfer Characteristics

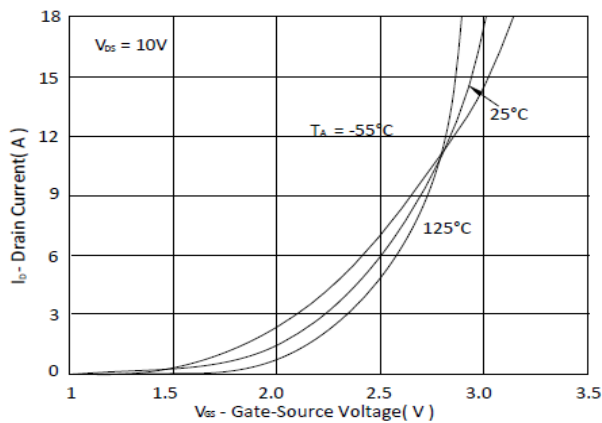


Figure 6. Typical Source-Drain Diode Forward Voltage

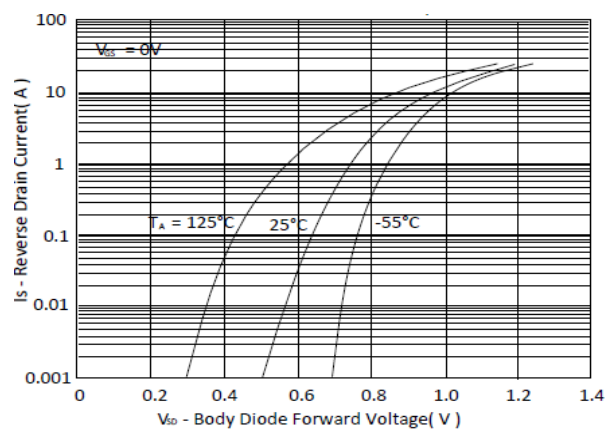


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

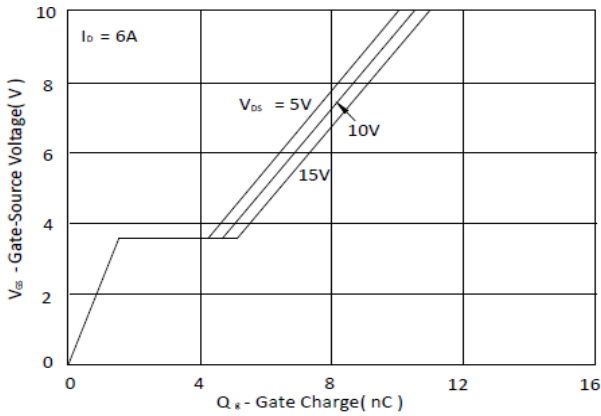


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

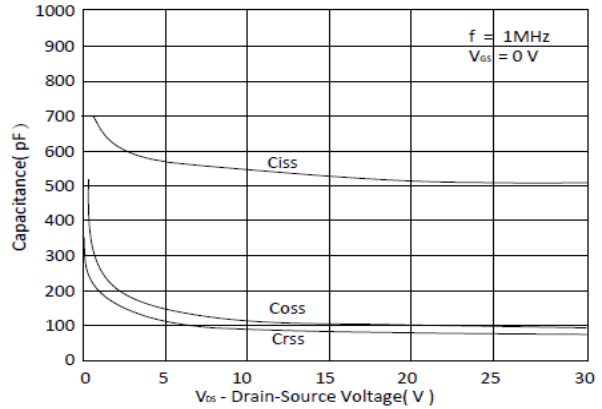


Figure 9. Maximum Safe Operating Area

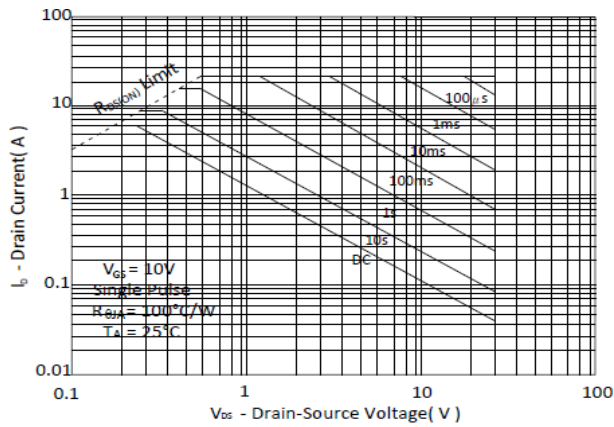


Figure 10. Single Pulse Maximum Power Dissipation

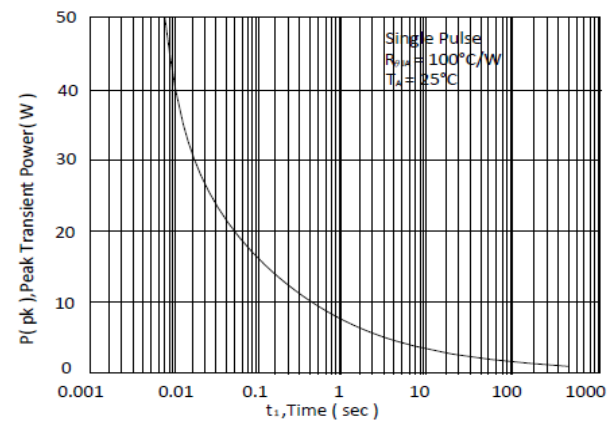
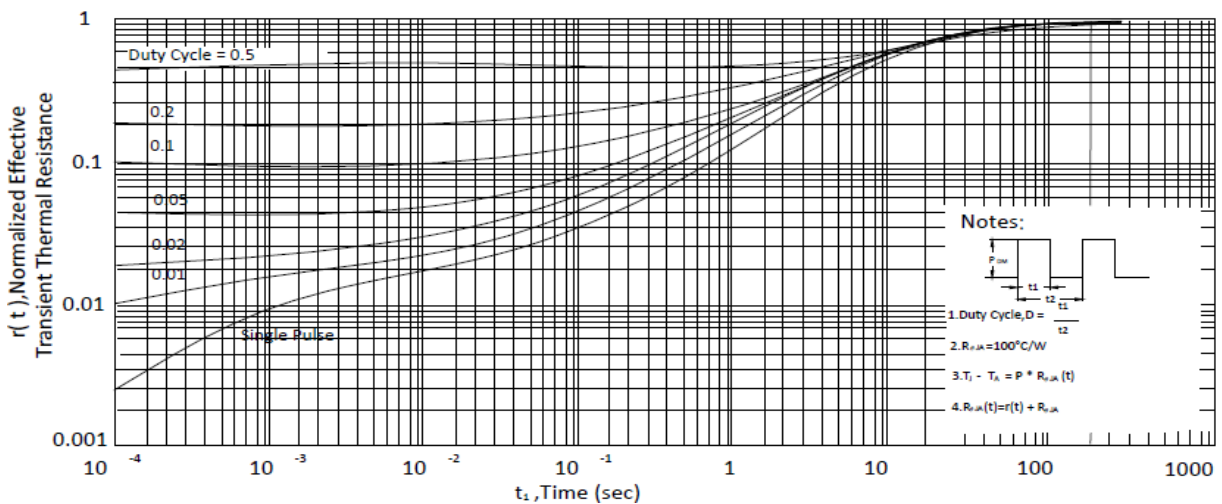
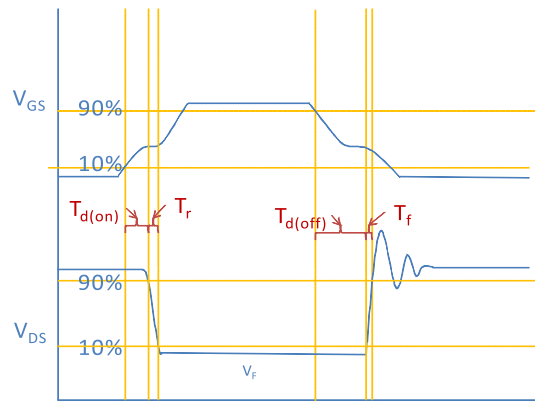
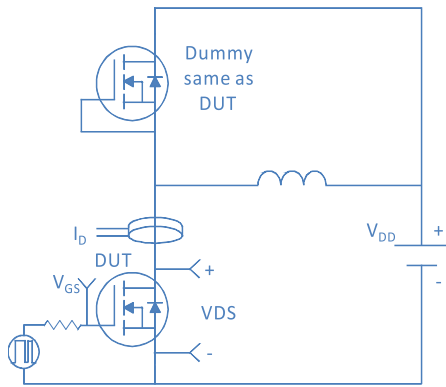


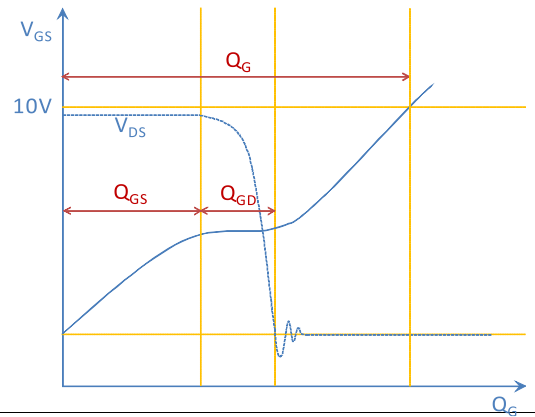
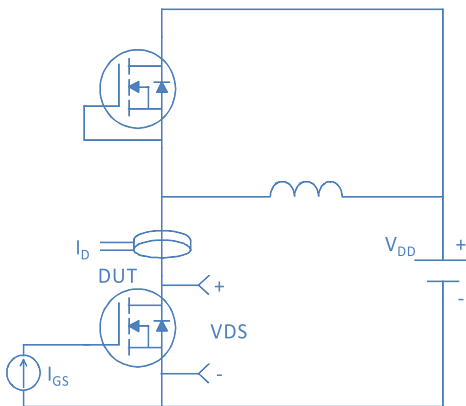
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



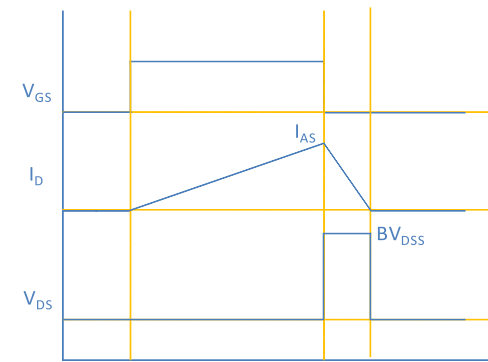
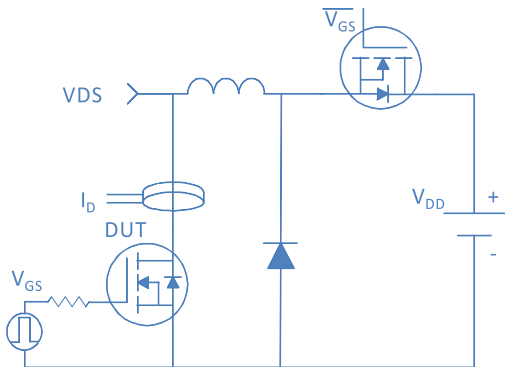
Inductive switching Test



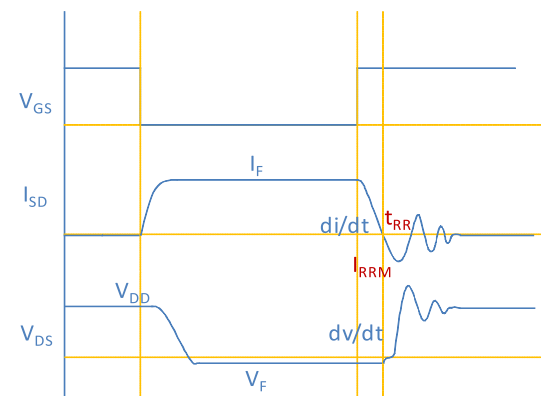
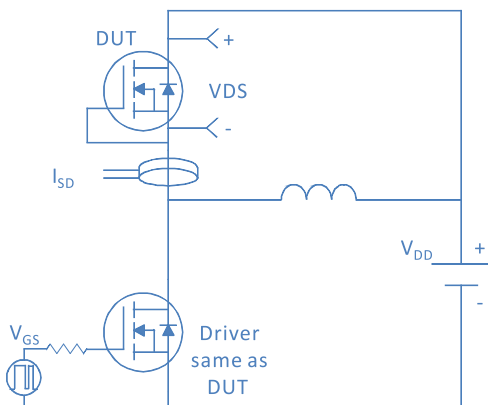
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

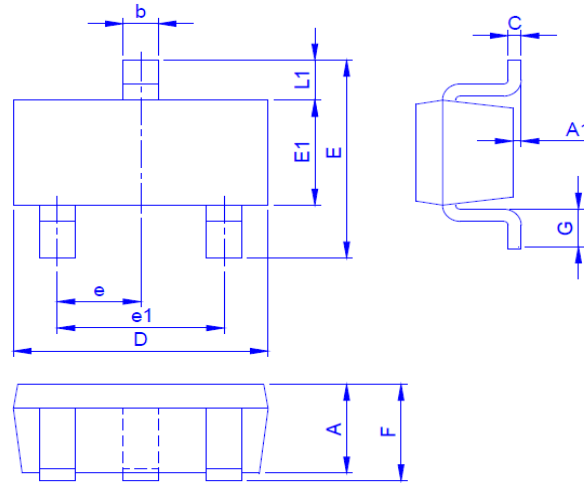


Diode Recovery Test



Package Outline

SOT-23, 3leads



Dimension in mm

Dimension	A	A1	A2	b	C	D	E	E1	e	e1	F	G	L1
Min.	0.7	0		0.35	0.1	2.8	2.6	1.5	0.9		0.8	0.3	0.55
Typ.						2.9	2.8	1.6	0.95	1.9			
Max.	1.12	0.1		0.5	0.2	3	3	1.7	1		1.2	0.6	0.65